TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# HN1K02FU

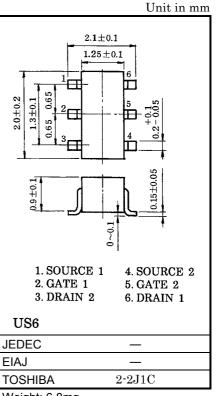
**High Speed Switching Applications** Analog Switch Applications

- 2.5 V gate drive.
- Low threshold voltage:  $V_{th} = 0.5V \sim 1.5V$
- High speed
- Enhancement-mode
- Small package

#### Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Drain-Source voltage	$V_{DS}$	20	V
Gate-Source voltage	V <sub>GSS</sub>	10	V
DC Drain current	I <sub>D</sub>	50	mA
Drain power dissipation	P <sub>D</sub> *	200	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Total rating



Weight: 6.8mg

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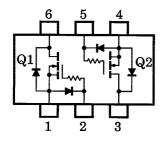
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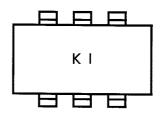
### Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

Charae	cteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0	_	_	1	μΑ
Drain-Source breakdown voltage		V (BR) DSS	I <sub>D</sub> = 100μA, V <sub>GS</sub> = 0	20	_	_	V
Drain cut-off curr	rent	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0	_	_	1	μΑ
Gate threshold v	oltage	V <sub>th</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 0.1mA	0.5	_	1.5	V
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA	20	_	_	mS
Drain-Source ON	N resistance	R <sub>DS</sub> (ON)	I <sub>D</sub> = 10mA, V <sub>GS</sub> = 2.5V	_	20	40	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3V, V_{GS} = 0,$ f = 1MHz	_	5.5	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 3V, V_{GS} = 0,$ f = 1MHz	_	1.6	_	pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3V, V_{GS} = 0,$ f = 1MHz	_	6.5	_	pF
Switching time	Turn-on time	t <sub>on</sub>	V <sub>DD</sub> = 3V, I <sub>D</sub> = 10mA, V <sub>GS</sub> = 0~2.5V	_	0.14	_	μs
	Turn-off time	t <sub>off</sub>	V <sub>DD</sub> = 3V, I <sub>D</sub> = 10mA, V <sub>GS</sub> = 0~2.5V	_	0.14	_	μs

## **Equivalent Circuit (Top View)**

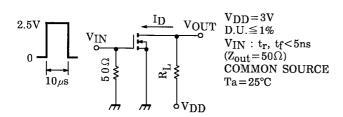


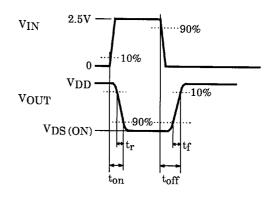
### Marking

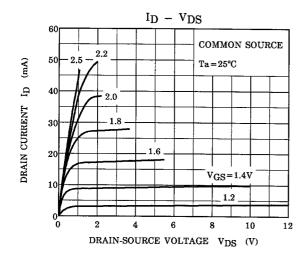


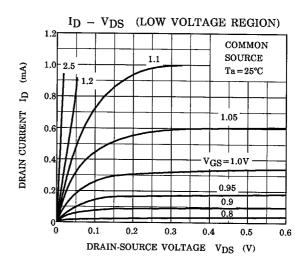
### (Q1,Q2 Common)

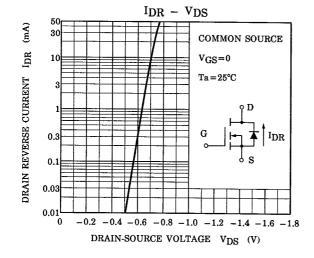
### **Switching Time Test Circuit**

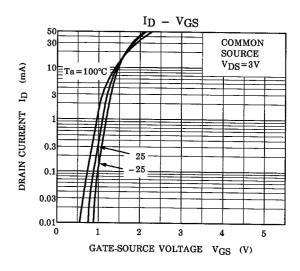




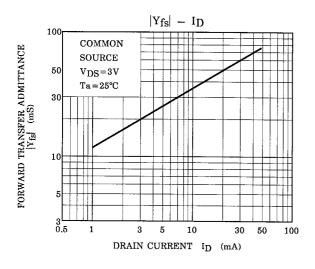


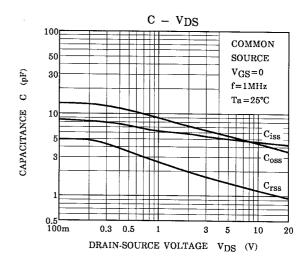


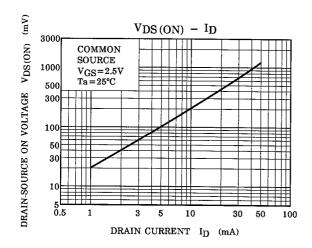


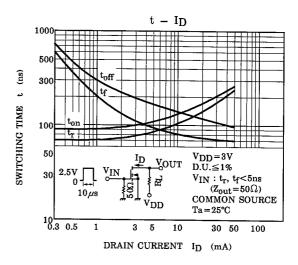


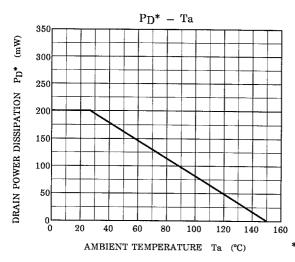
#### (Q1,Q2 Common)











\* : Total Rating